

ABSTRACT OF THE DISCLOSURE

HIGH ASPECT RATIO ETCH WITH COMBINATION MASK

5 A method for etching features in a stack is provided. A combination hardmask is formed by forming a first hardmask layer comprising carbon or silicon oxide over the stack, forming a second hardmask layer comprising metal over the first hardmask layer, and patterning the first and second hardmask layers. The stack is etched through the combination hardmask.

10 FIG. 1